

# Pj Zampardi

## List of Publications by Year in descending order

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18  
papers

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1163117

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14  
g-index

18  
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18  
docs citations

18  
times ranked

110  
citing authors

#	ARTICLE	IF	CITATIONS
1	Technology design interaction. , 2016, , 209-259.		0
2	A GaAs Junction Varactor With a Continuously Tunable Range of 9â€‰%:â€‰%1 and an \$OIP_{3}\$ of 57 dBm. IEEE Electron Device Letters, 2010, 31, 108-110.	3.9	11
3	An InGaP/GaAs Merged HBT-FET (BiFET) Technology and Applications to the Design of Handset Power Amplifiers. IEEE Journal of Solid-State Circuits, 2007, 42, 2137-2148.	5.4	19
4	A Broad-Band Lumped Element Analytic Model Incorporating Skin Effect and Substrate Loss for Inductors and Inductor Like Components for Silicon Technology Performance Assessment and RFIC Design. IEEE Transactions on Electron Devices, 2005, 52, 1429-1441.	3.0	33
5	A comparison of linear handset power amplifiers in different bipolar technologies. IEEE Journal of Solid-State Circuits, 2004, 39, 1746-1754.	5.4	54
6	16 GHz low-power 1:4 prescaler fabricated in 1.0 [micro sign]m BiFET technology. Electronics Letters, 2001, 37, 389.	1.0	1
7	High performance Al/sub 0.35/Ga/sub 0.65/As/GaAs HBT's. IEEE Electron Device Letters, 2000, 21, 196-199.	3.9	11
8	Heterostructure-based high-speed/high-frequency electronic circuit applications. Solid-State Electronics, 1999, 43, 1633-1643.	1.4	4
9	Role of neutral base recombination in high gain AlGaAs/GaAs HBT's. IEEE Transactions on Electron Devices, 1999, 46, 1599-1607.	3.0	14
10	30 Gbit/s 1:4 demultiplexer IC using AlGaAs/GaAs HBTs. Electronics Letters, 1997, 33, 765.	1.0	5
11	Ultra Highspeed AlGaAs/GaAs HBT Circuits For Up To 40 Gb/s Optical Communications. , 1997, , .		3
12	A packaged broad-band monolithic variable gain amplifier implemented in AlGaAs/GaAs HBT technology. IEEE Journal of Solid-State Circuits, 1996, 31, 1380-1387.	5.4	5
13	Delay of Kirk effect due to collector current spreading in heterojunction bipolar transistors. IEEE Electron Device Letters, 1996, 17, 470-472.	3.9	18
14	Packaged 30 Gbit/s data demultiplexing and clock extraction IC fabricated in a AlGaAs/GaAs HBT technology. Electronics Letters, 1996, 32, 588.	1.0	6
15	40 Gbit/s AlGaAs/GaAs HBT 4:1 multiplexer IC. Electronics Letters, 1995, 31, 876-877.	1.0	28
16	Circuit demonstrations in a GaAs BiFET technology. Solid-State Electronics, 1995, 38, 1723-1726.	1.4	1
17	Monolithically integrated HBT/MESFET circuit. Electronics Letters, 1993, 29, 1100.	1.0	2
18	High efficiency current-mode class-D amplifier with integrated resonator. , 0, , .		4